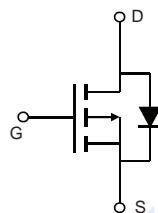
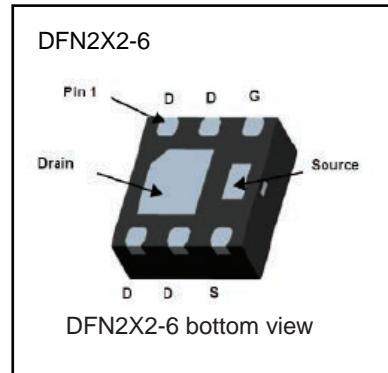


P-channel MOSFET

2KJ6053DFN

■ Features

- V_{DS} -20V
- I_D (at $V_{GS}=-4.5V$) -4A
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) < 100m Ω
- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) < 140m Ω

■ Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted.)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current	$TA=25^\circ C$	I_D	-4	A
	$TA=70^\circ C$		-2.4	
Pulsed Drain Current		I_{DM}	-14	
Power Dissipation	$TA=25^\circ C$	P_D	0.7	W
	$TA=70^\circ C$		0.45	
Thermal Resistance.Junction- to-Ambient		$R_{\theta JA}$	175	$^\circ C/W$
Junction Temperature		T_J	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 to 150	

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■ Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{Id} = -250\mu\text{A}, \text{V}_{\text{GS}} = 0\text{V}$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}} = -20\text{V}, \text{V}_{\text{GS}} = 0\text{V}$			-1	μA
		$\text{V}_{\text{DS}} = -20\text{V}, \text{V}_{\text{GS}} = 0\text{V}, \text{T}_J = 55^\circ\text{C}$			-5	
Gate-Body Leakage Current	I_{GSS}	$\text{V}_{\text{DS}} = 0\text{V}, \text{V}_{\text{GS}} = \pm 8\text{V}$			± 100	nA
Gate Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}, \text{Id} = -250\mu\text{A}$	-0.4		-1.0	V
Static Drain-Source On-Resistance *	$\text{R}_{\text{DS(On)}}$	$\text{V}_{\text{GS}} = -4.5\text{V}, \text{Id} = -2.8\text{A}$			100	$\text{m}\Omega$
		$\text{V}_{\text{GS}} = -2.5\text{V}, \text{Id} = -2\text{A}$			140	
Input Capacitance	C_{iss}	$\text{V}_{\text{GS}} = 0\text{V}, \text{V}_{\text{DS}} = -15\text{V}, \text{f} = 1\text{MHz}$		480		pF
Output Capacitance	C_{oss}			46		
Reverse Transfer Capacitance	C_{rss}			10		
Total Gate Charge	Q_{g}	$\text{V}_{\text{DS}} = -6\text{V}, \text{Id} = -2.8\text{A}$ $\text{V}_{\text{GS}} = -4.5\text{V}$		7.2		nC
Gate Source Charge	Q_{gs}			2.2		
Gate Drain Charge	Q_{gd}			1.2		
Turn-On Delay Time	$\text{t}_{\text{d(on)}}$	$\text{V}_{\text{GS}} = -4.5\text{V}, \text{V}_{\text{DS}} = -6\text{V}, \text{RL} = 6\Omega, \text{R}_{\text{GEN}} = 6\Omega$		50		ns
Turn-On Rise Time	t_{r}			30		
Turn-Off Delay Time	$\text{t}_{\text{d(off)}}$			40		
Turn-Off Fall Time	t_{f}			11		
Diode Forward Voltage	V_{SD}	$\text{Is} = -1 \text{ A}, \text{V}_{\text{GS}} = 0\text{V}$			-1.2	V

* Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

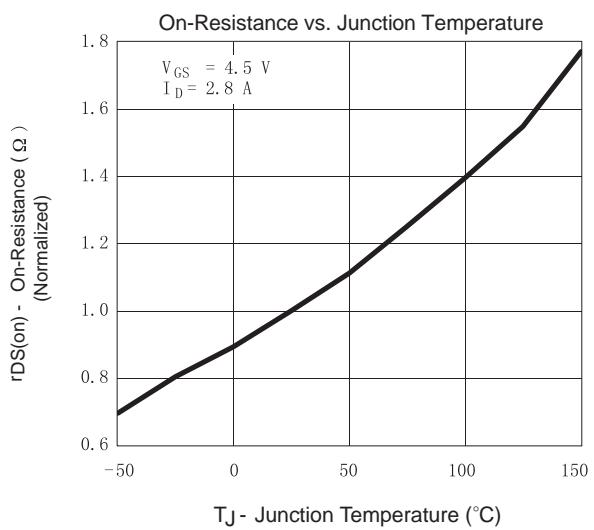
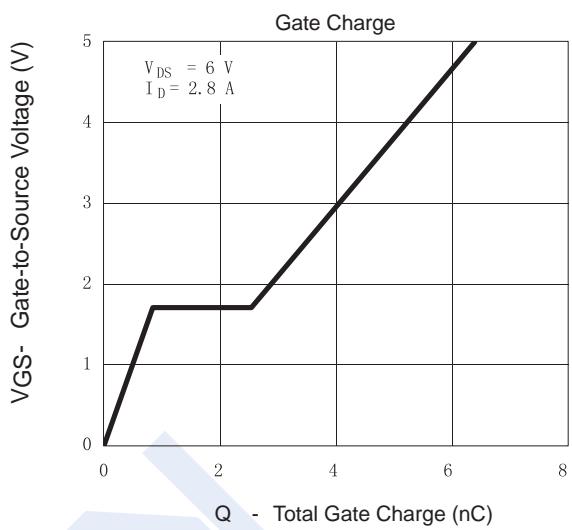
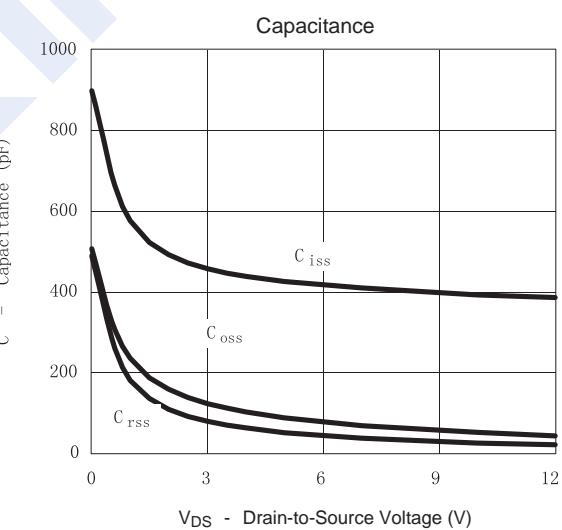
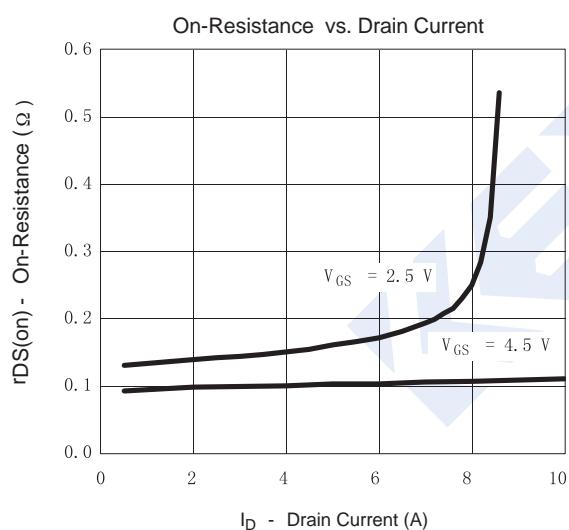
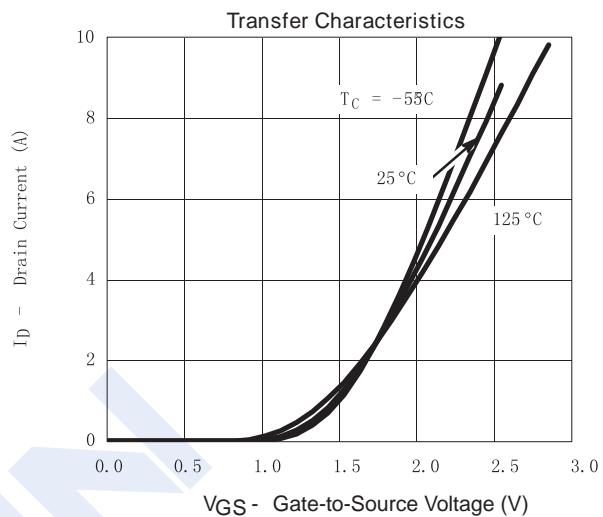
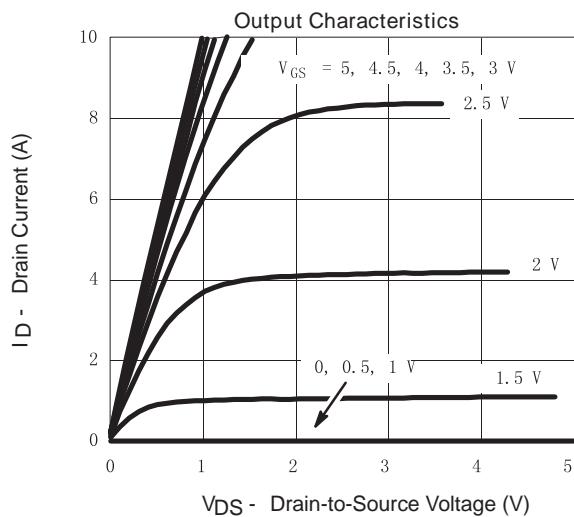
■ Marking

Marking	JCA
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P-channel MOSFET

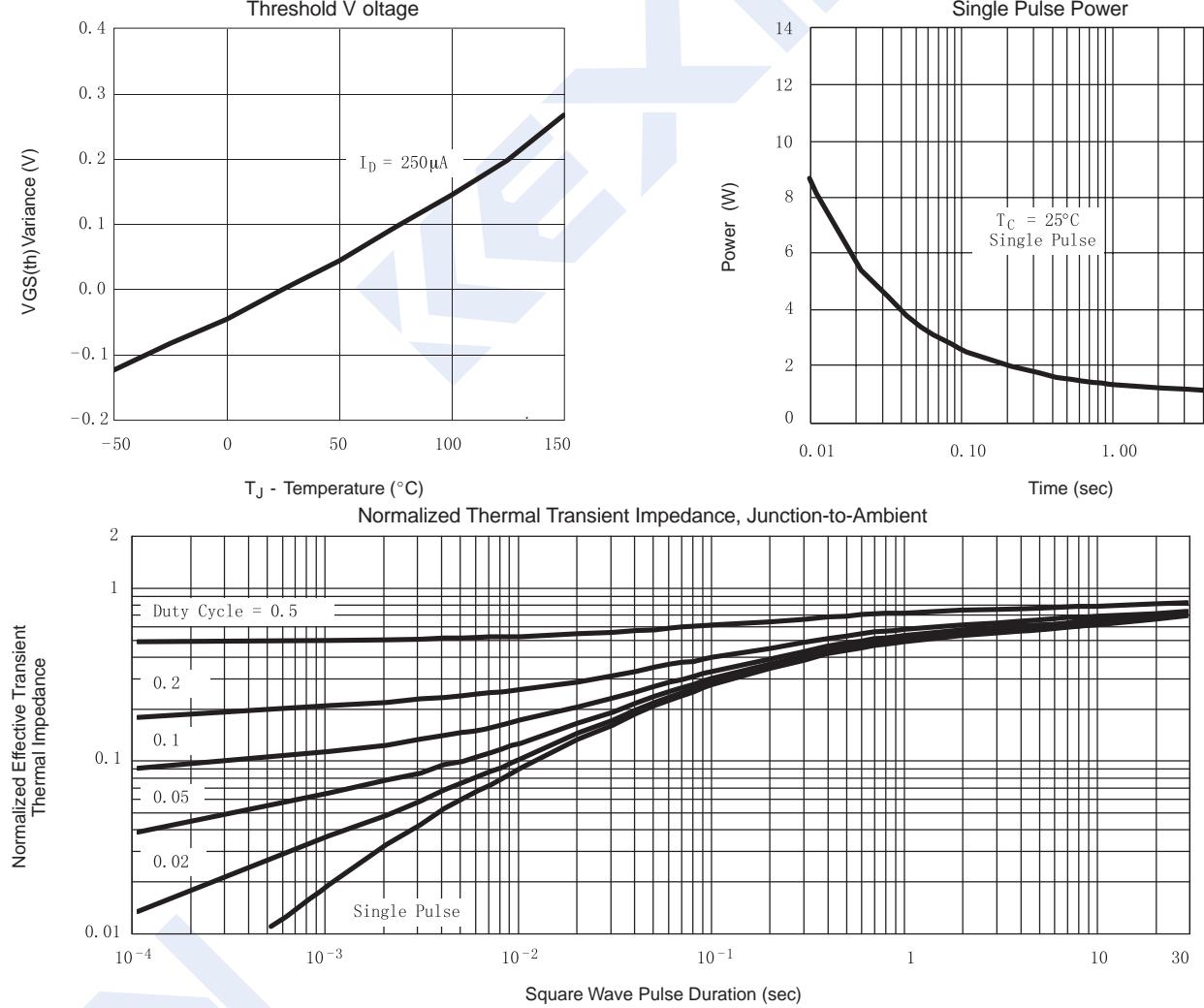
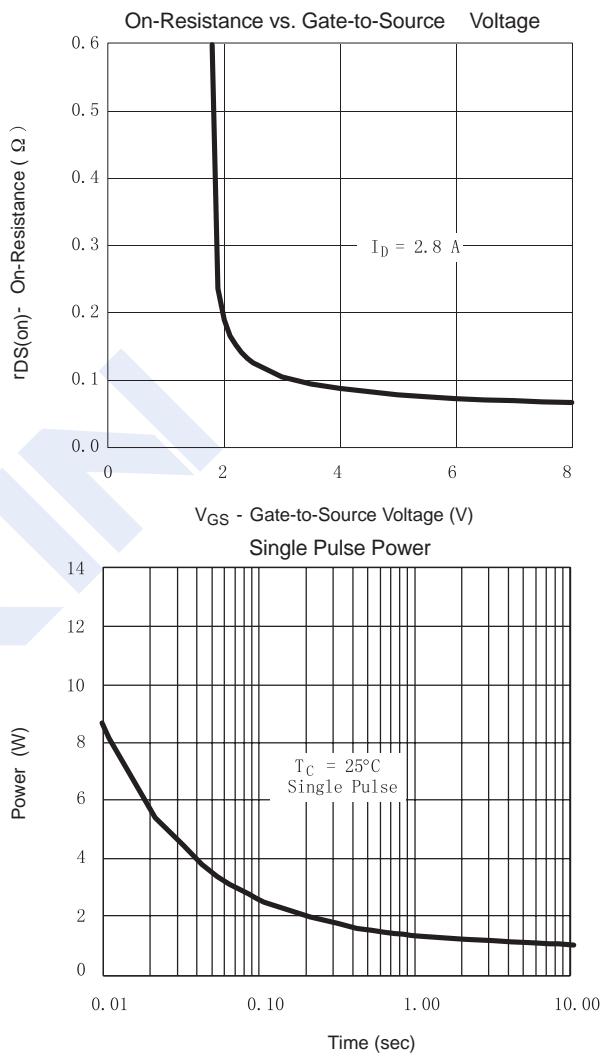
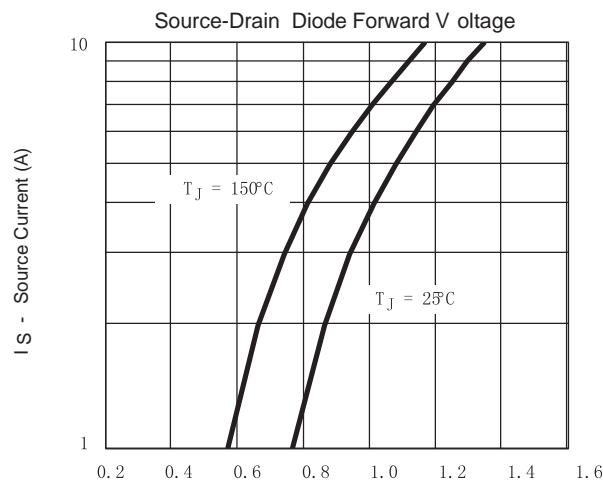
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■ Typical Characteristics



P-channel MOSFET

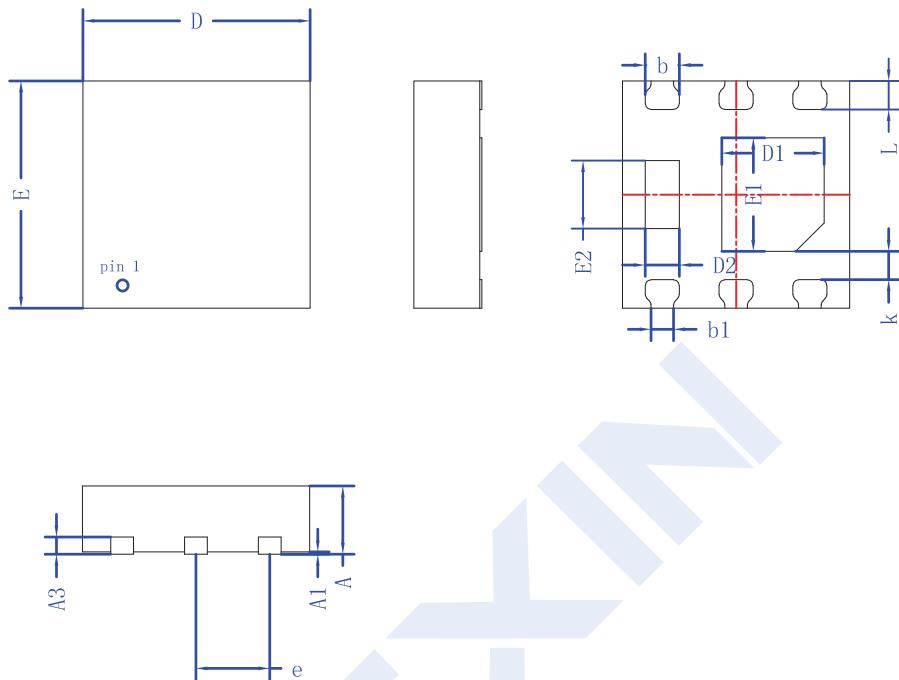
2KJ6053DFN



P-channel MOSFET

2KJ6053DFN

■ DFN2X2-6 Package Outline Dimensions



Symbol	Dimensions In Millimeters			Dimensions In Inches			
	Min.	Typ.	Max.	Min.	Typ.	Max.	
A	0.50	0.55	0.65	0.022	0.024	0.026	
A1	0.00	0.02	0.05	0.000	0.001	0.002	
A3	0.152 REF.			0.006REF.			
D	1.90	2.00	2.10	0.075	0.079	0.083	
D1	0.80	0.90	1.00	0.031	0.035	0.039	
D2	0.20	0.30	0.40	0.008	0.012	0.016	
E	1.90	2.00	2.10	0.075	0.079	0.083	
E1	0.90	1.00	1.10	0.035	0.039	0.043	
E2	0.50	0.60	0.70	0.020	0.024	0.028	
b	0.25	0.30	0.35	0.010	0.012	0.014	
b1	0.15	0.20	0.25	0.006	0.008	0.010	
e	0.65TYP.			0.026TYP.			
k	0.20MIN.			0.006MIN.			
L	0.20	0.25	0.30	0.008	0.010	0.012	